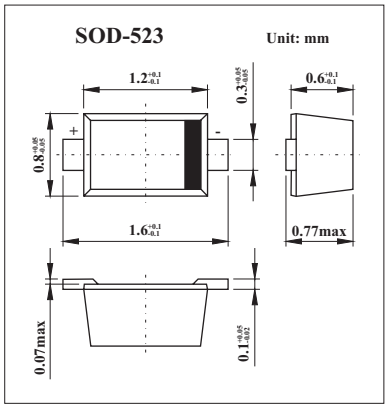
Silicon RF Switching Diode

BAR65-02W



Features

- Low loss, low capacitance PIN-diode
- Band switch for TV-tuners
- Series diode for mobile communication transmit-receiver switch

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Value	Unit
Diode reverse voltage	V_R	30	V
Forward current	I_F	100	mA
Operating temperature range	T_{op}	-55 to +125	℃
Storage temperature	T_{stg}	-55 to +150	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse current	V_R	V_R = 20 V			20	nA
Forward voltage	V_F	I_F = 100 mA		0.93	1	V
Diode capacitance	C_T	V_R = 1 V, f = 1 MHz		0.6	0.9	pF
		V_R = 3 V, f = 1 MHz		0.57	0.8	
Forward resistance	r_f	I_F = 5 mA, f = 100 MHz		0.65	0.95	Ω
		I_F = 10 mA, f = 100 MHz		0.56	0.9	
Series inductance	Ls			0.6		nH

Marking

Marking	N